

Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

Claim 1 (original): A method for forming a conductor on a dielectric, comprising:

- a) depositing a conductive thickfilm on the dielectric;
- b) subsintering the conductive thickfilm;
- c) patterning the conductive thickfilm to define at least one conductor;
- d) etching the conductive thickfilm to expose the at least one conductor;
- and
- e) firing the at least one conductor at a full sintering temperature.

Claim 2 (original): The method of claim 1, wherein the conductive thickfilm comprises gold.

Claim 3 (canceled)

Claim 4 (original): The method of claim 1, wherein the dielectric is a glass dielectric.

Claim 5 (canceled)

Claim 6 (original): The method of claim 1, wherein said subsintering comprises subsintering at a peak temperature of about 725°C for about ten minutes.

Claim 7 (currently amended): The method of claim 6, wherein the conductive thickfilm comprises gold and the dielectric comprises a [[KQ dielectric]]borosilicate

glass-based material with a dielectric constant of about 3.9 and a loss tangent of about 1×10^{-4} .

Claim 8 (canceled).

Claim 9 (original): The method of claim 1, wherein said subsintering comprises subsintering at a peak temperature between 725°C and 850°C.

Claim 10 (currently amended): The method of claim 9, wherein the conductive thickfilm comprises gold and the dielectric comprises a [[KQ dielectric]]borosilicate glass-based material with a dielectric constant of about 3.9 and a loss tangent of about 1×10^{-4} .

Claim 11 (canceled)

Claim 12 (original): The method of claim 1, further comprising depositing the conductive thickfilm on a substrate at about the same time the conductive thickfilm is deposited on the glass dielectric.

Claim 13 (original): The method of claim 12, wherein the substrate is an alumina ceramic substrate.

Claim 14 (original): The method of claim 12, wherein the subsintering is undertaken at a peak temperature that equalizes the etch rates of the conductive thickfilm on the substrate and the glass dielectric.

Claim 15 (canceled)

Claim 16 (original): The method of claim 14, wherein said subsintering comprises subsintering at a peak temperature of about 725°C for about ten minutes.

Claim 17 (currently amended): The method of claim 16, wherein the conductive thickfilm comprises gold and the dielectric comprises a [[KQ dielectric]]borosilicate glass-based material with a dielectric constant of about 3.9 and a loss tangent of about 1×10^{-4} .

Claim 18 (original): The method of claim 17, wherein the substrate is an alumina ceramic substrate.

Claim 19 (original): The method of claim 14, wherein said subsintering comprises subsintering at a peak temperature between 700°C and 850°C.

Claim 20 (original): The method of claim 1, further comprising, after firing, dipping the at least one conductor in an unheated solution of 10:1 hydrofluoric acid to de-ionized water for about ten seconds, and then rinsing the at least one conductor in de-ionized water.